To all our customers

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Renesas Technology Home Page: http://www.renesas.com

Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

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   Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SK2116, 2SK2117

Silicon N-Channel MOS FET

November 1996

Application

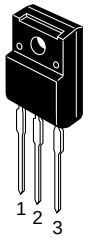
High speed power switching

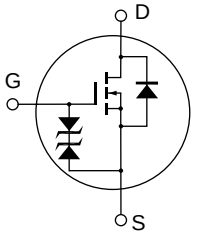
Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for Switching regulator

Outline

TO-220CFM





1. Gate
2. Drain
3. Source

Ordering Information

Type No.	V_{DSS}
2SK2116	450 V
2SK2117	500 V

Absolute Maximum Ratings (Ta = 25°C)

Item		Symbol	Ratings	Unit
Drain to source voltage	2SK2116	V_{DSS}	450	V
	2SK2117	V_{DSS}	500	
Gate to source voltage		V_{GSS}	±30	V
Drain current		I_D	7	A
Drain peak current		$I_{D(pulse)}$*[1]	28	A
Body to drain diode reverse drain current		I_{DR}	7	A
Channel dissipation		Pch*[2]	35	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	–55 to +150	°C

Notes 1. PW ≤ 10 µs, duty cycle ≤ 1 %
2. Value at Tc = 25 °C

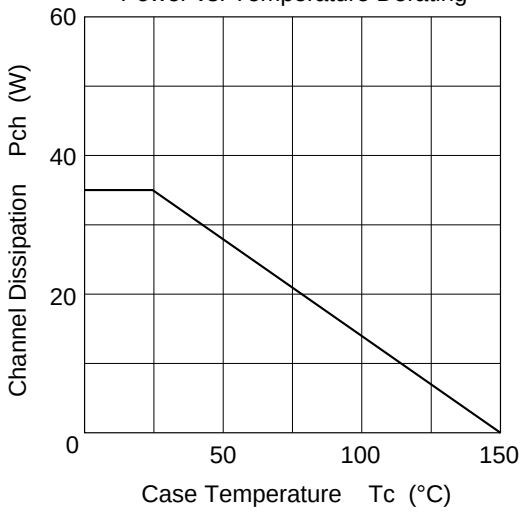
Electrical Characteristics (Ta = 25°C)

Item		Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	2SK2116	$V_{(BR)DSS}$	450	—	—	V	I_D = 10 mA, V_{GS} = 0
	2SK2117		500				
Gate to source breakdown voltage		$V_{(BR)GSS}$	±30	—	—	V	I_G = ±100 µA, V_{DS} = 0
Gate to source leak current		I_{GSS}	—	—	±10	µA	V_{GS} = ±25 V, V_{DS} = 0
Zero gate voltage drain current	2SK2116	I_{DSS}	—	—	250	µA	V_{DS} = 360 V, V_{GS} = 0
	2SK2117						V_{DS} = 400 V, V_{GS} = 0
Gate to source cutoff voltage		$V_{GS(off)}$	2.0	—	3.0	V	I_D = 1 mA, V_{DS} = 10 V
Static drain to source on state resistance	2SK2116	$R_{DS(on)}$	—	0.6	0.8	Ω	I_D = 4 A, V_{GS} = 10 V*[1]
	2SK2117		—	0.7	0.9		
Forward transfer admittance		$\|y_{fs}\|$	4.0	6.5	—	S	I_D = 4 A V_{DS} = 10 V*[1]
Input capacitance		Ciss	—	1050	—	pF	V_{DS} = 10 V
Output capacitance		Coss	—	280	—	pF	V_{GS} = 0
Reverse transfer capacitance		Crss	—	40	—	pF	f = 1 MHz
Turn-on delay time		$t_{d(on)}$	—	15	—	ns	I_D = 4 A
Rise time		t_r	—	55	—	ns	V_{GS} = 10 V
Turn-off delay time		$t_{d(off)}$	—	95	—	ns	R_L = 7.5 Ω
Fall time		t_f	—	40	—	ns	
Body to drain diode forward voltage		V_{DF}	—	0.95	—	V	I_F = 7 A, V_{GS} = 0
Body to drain diode reverse recovery time		t_{rr}	—	320	—	ns	I_F = 7 A, V_{GS} = 0, diF / dt = 100 A / µs

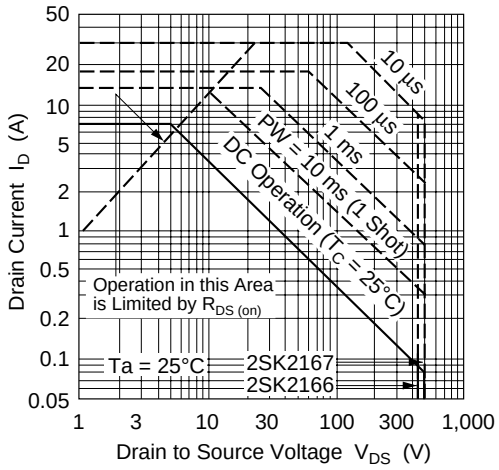
Note 1. Pulse Test

See characteristic curve of 2SK1157, 2SK1158.

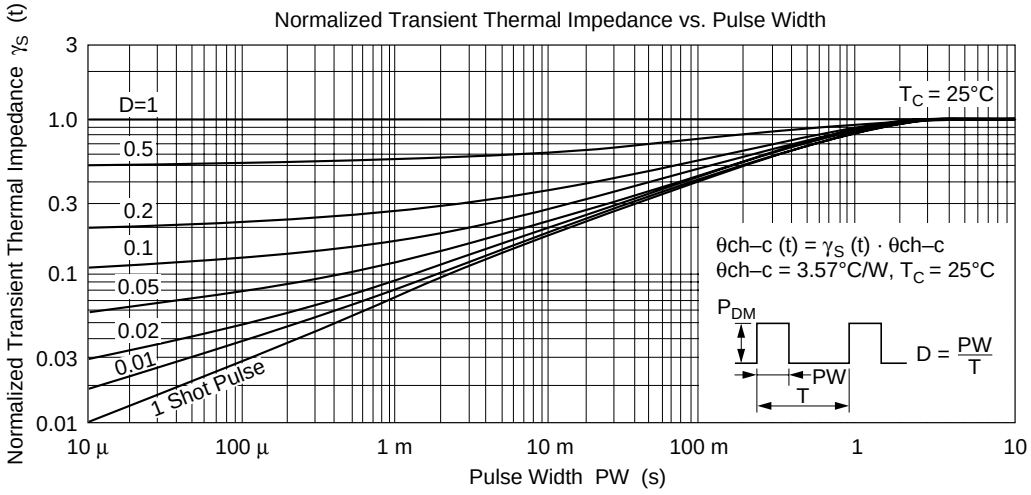
Power vs. Temperature Derating



Maximum Safe Operation Area



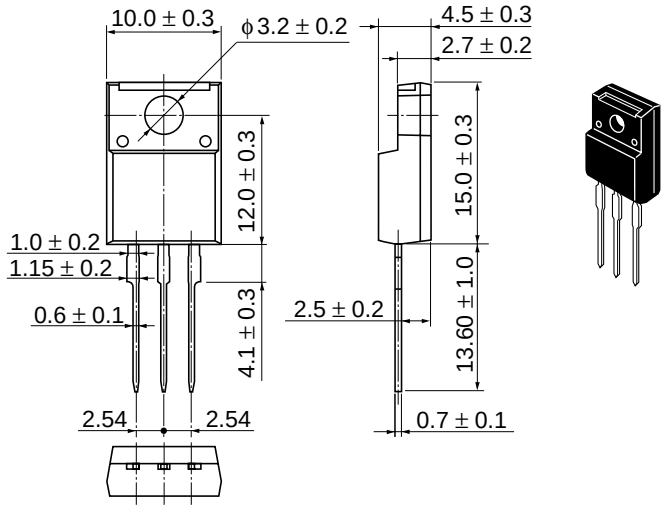
Normalized Transient Thermal Impedance vs. Pulse Width



Package Dimensions

As of January, 2001

Unit: mm



Hitachi Code	TO-220CFM
JEDEC	—
EIAJ	—
Mass (reference value)	1.9 g

Cautions

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HITACHI

Hitachi, Ltd.
Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL NorthAmerica : http://semiconductor.hitachi.com/
Europe : http://www.hitachi-eu.com/hel/ecg
Asia : http://sicapac.hitachi-asia.com
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For further information write to:

Hitachi Semiconductor (America) Inc.
179 East Tasman Drive,
San Jose,CA 95134
Tel: <1> (408) 433-1990
Fax: <1>(408) 433-0223

Hitachi Europe GmbH
Electronic Components Group
Dornacher Straβe 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 585160

Hitachi Asia Ltd.
Hitachi Tower
16 Collyer Quay #20-00,
Singapore 049318
Tel : <65>-538-6533/538-8577
Fax : <65>-538-6933/538-3877
URL : http://www.hitachi.com.sg

Hitachi Asia Ltd.
(Taipei Branch Office)
4/F, No. 167, Tun Hwa North Road,
Hung-Kuo Building,
Taipei (105), Taiwan
Tel : <886>-(2)-2718-3666
Fax : <886>-(2)-2718-8180
Telex : 23222 HAS-TP
URL : http://www.hitachi.com.tw

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon,
Hong Kong
Tel : <852>-(2)-735-9218
Fax : <852>-(2)-730-0281
URL : http://www.hitachi.com.hk

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